The modulus chilled multiple PD

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The results of operations to creation of moduluss matrix PD format 4(2884), topology - multirow bar, pixel - 2528 мкм2) are introduced. The justification of technological conditions of fabrication p-n in epitaxial and heteroepitaxial patterns with veryzone by strata is given. The construction of a photodetector is designed. The specification statement of the multiplexer for PD is reduced. The technological track p-n and construction of a photodetector is designed. The specification statement a construction of a cryostat, and also specification statement of gaging machinery is reduced. The following results are obtained: Is selected optimal, from the point of view of conditions of beaming, method of an ionic implantation conduction, applied for inverse, of patterns; The supervisory equipment of photoelectric arguments of photodetectors supplying measurings of responsiveness and threshold performances created, both experimental is model of countermeasure feelers, and multiple patterns, сoincidence with the multiplexer; The studies are held and the trade - off of a construction PD is realized; The manufacturing process of fabrication of a photodiode array PD on a ground(basis) MIE MCT and chilled silicon multiplexer designed; The construction of a cryostat reducing wormstrum to PD up to 1,3Вт is designed; Samples PD with arguments manufactured: - Mean specific detectivity in a maxima of spectral responsivety not less than

9,51010смГц1/2Вт1, - Wave length of a maxima of spectral responsiveness 9,8 microns,- Amount of the signal deductions - 8,- Working temperature - 80К,-V-W Responsiveness in maxima of spectral responsiveness at time of integrating 20 µs not less 8107 V / W.